**Product data sheet** 

## 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- · Low threshold voltage
- Trench MOSFET technology
- Side wettable flanks for optical solder inspection
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- · Exposed drain pad for excellent thermal conduction

## 3. Applications

- · Charging switch for portable devices
- DC-to-DC converters
- Power management in battery-driven portable devices
- · Hard disk and computing power management

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-12	V	
$V_{GS}$	gate-source voltage			-8	-	8	V	
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	-	-12.7	Α	
Static characte	Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -8.6 \text{ A}; T_j = 25 \text{ °C}$		-	14	19	mΩ	

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



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# 5. Pinning information

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	1 1 1 1 6	D -
2	D	drain		
3	G	gate	2 5	
4	S	source	3 8 94	s
5	D	drain	Transparent top view	017aaa094
6	D	drain	DFN2020MD-6 (SOT1220)	
7	D	drain		
8	S	source		

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package					
	Name	Description	Version			
PMPB14XP	DFN2020MD-6	DFN2020MD-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220			

# 7. Marking

#### **Table 4. Marking codes**

Type number	Marking code
PMPB14XP	5B

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# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-12	V
$V_{GS}$	gate-source voltage			-8	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	-12.7	А
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-8.6	А
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	-5.4	А
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-35	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[1]	-	1.8	W
		T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	3.9	W
		T <sub>sp</sub> = 25 °C		-	15.6	W
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drain	n diode					
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	-1.6	Α

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

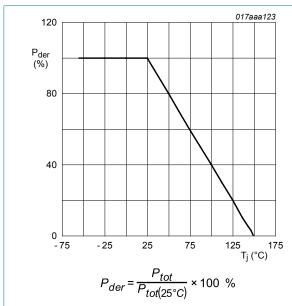


Fig. 1. Normalized total power dissipation as a function of junction temperature

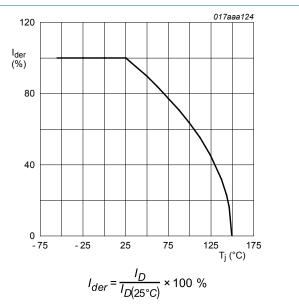


Fig. 2. Normalized continuous drain current as a function of junction temperature

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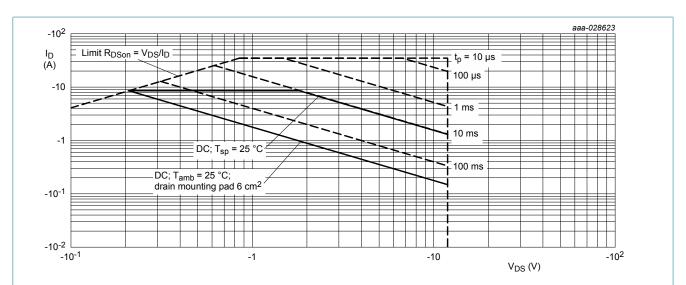


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

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### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance		[1]	-	226	260	K/W
	from junction to ambient		[2]	-	60	70	K/W
		in free air; t ≤ 5 s	[2]	-	27	32	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	4	8	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

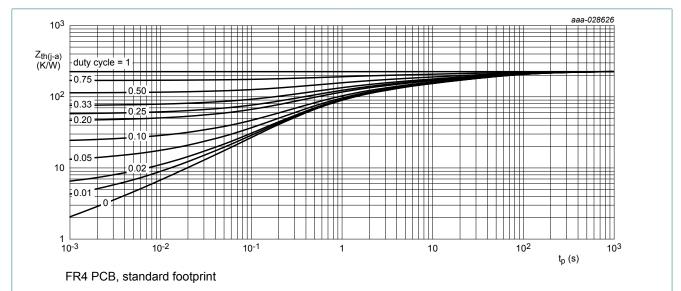
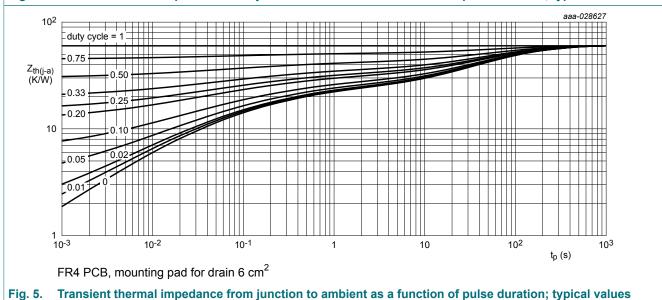


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



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## 10. Characteristics

#### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-12	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D$ = -250 $\mu$ A; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C	-0.45	-0.68	-0.9	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = -12 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = -8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-100	nA
		V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = -4.5 V; $I_D$ = -8.6 A; $T_j$ = 25 °C	-	14	19	mΩ
	resistance	V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -8.6 A; T <sub>j</sub> = 150 °C	-	18	24	mΩ
		$V_{GS}$ = -2.5 V; $I_{D}$ = -3.9 A; $T_{j}$ = 25 °C	-	19	25	mΩ
		V <sub>GS</sub> = -1.8 V; I <sub>D</sub> = -1 A; T <sub>j</sub> = 25 °C	-	24	42	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = -10 V; $I_D$ = -8.6 A; $T_j$ = 25 °C	-	92	-	S
$R_G$	gate resistance	f = 1 MHz	-	5.4	-	Ω
Dynamic ch	naracteristics				•	
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = -6 V; $I_{D}$ = -8.6 A; $V_{GS}$ = -4.5 V;	-	22	42	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	3.8	-	nC
Q <sub>GD</sub>	gate-drain charge		-	5.8	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = -6 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	2303	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	482	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	417	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -6 V; $I_{D}$ = -8.6 A; $V_{GS}$ = -4.5 V;	-	4	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	9	-	ns
t <sub>d(off)</sub>	turn-off delay time	_	-	64	-	ns
t <sub>f</sub>	fall time	$V_{DS}$ = -6 V; $I_{D}$ = -8.2 A; $V_{GS}$ = -4.5 V; $R_{G(ext)}$ = 6 $\Omega$ ; $T_{j}$ = 25 °C	-	36	-	ns
Source-dra	in diode		, ,		•	
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = -1.6 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-0.7	-1.2	V
					_	

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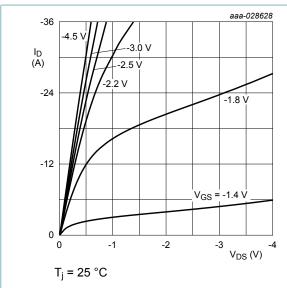


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

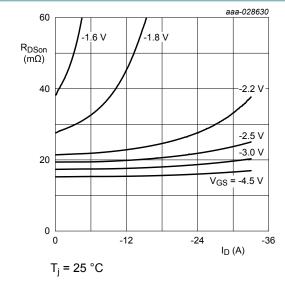


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

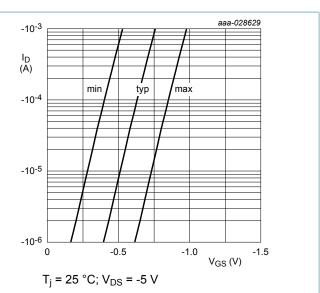


Fig. 7. Subthreshold drain current as a function of gate-source voltage

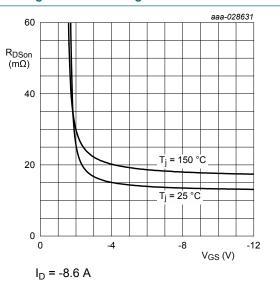


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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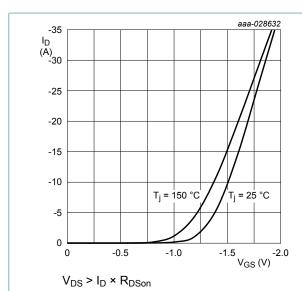


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

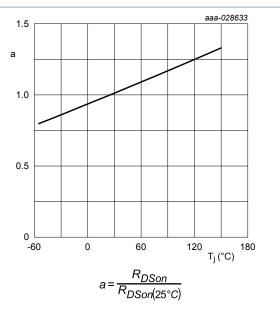


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

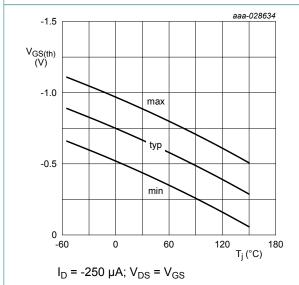


Fig. 12. Gate-source threshold voltage as a function of junction temperature

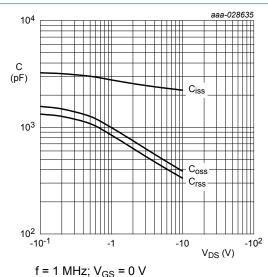


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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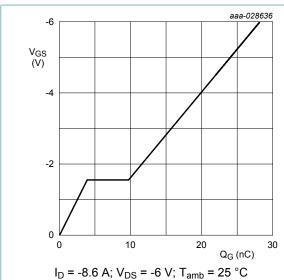


Fig. 14. Gate-source voltage as a function of gate

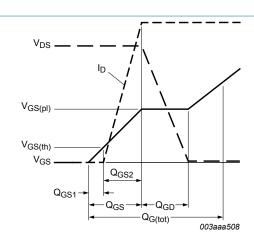


Fig. 15. Gate charge waveform definitions

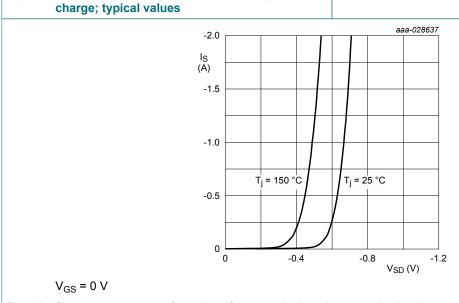
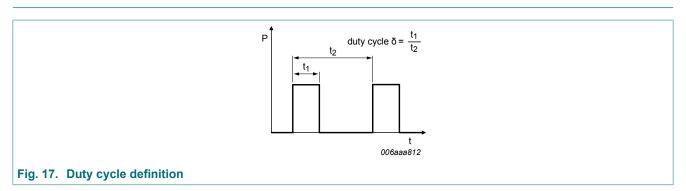


Fig. 16. Source current as a function of source-drain voltage; typical values

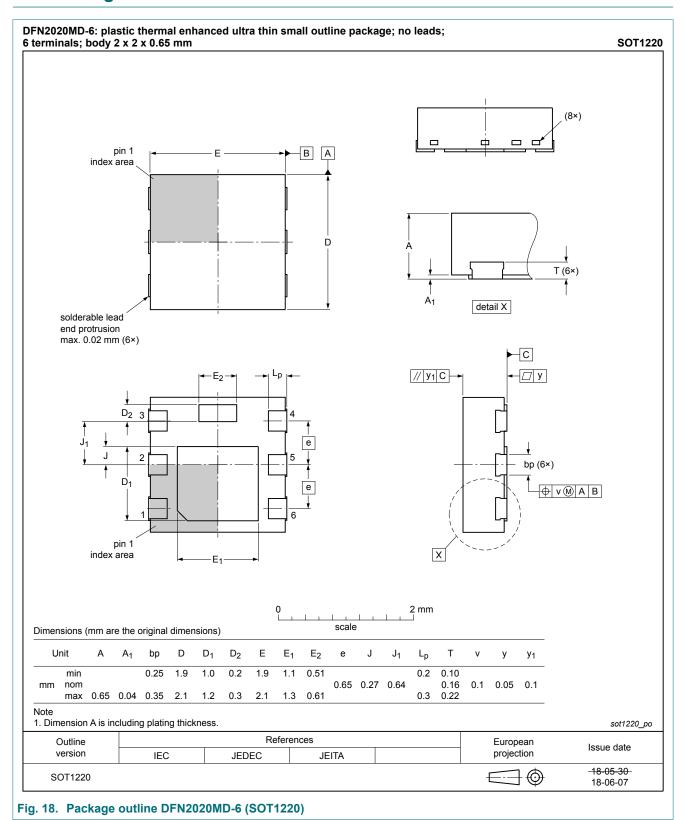
## 11. Test information



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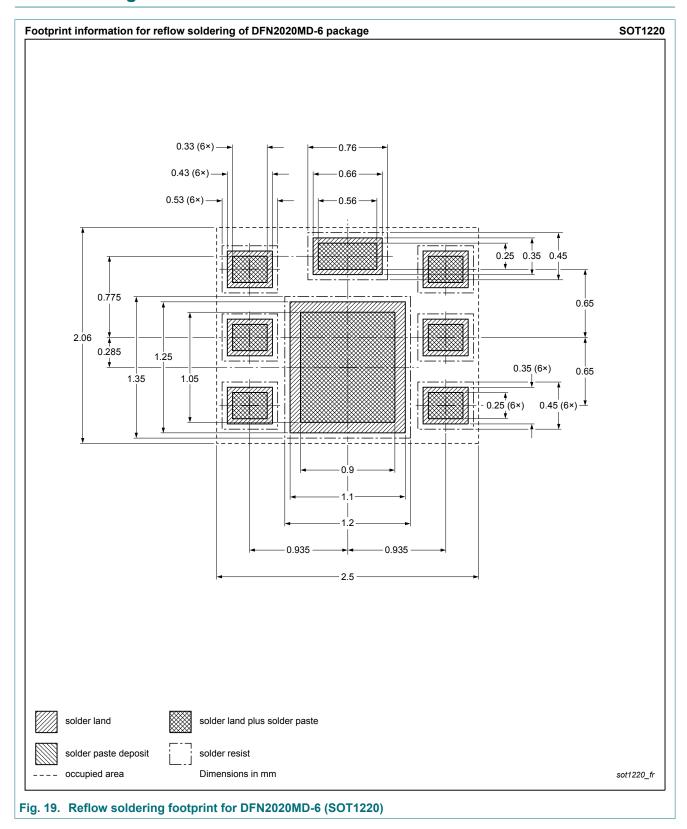
## 12. Package outline



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# 13. Soldering



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# 14. Revision history

### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMPB14XP v.1	20180703	Product data sheet	-	-

#### 12 V, P-channel Trench MOSFET

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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